



## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: David L. Bender  
Serial No.: 10/789,638  
Confirm. No. 9160  
Filed: Feb. 27, 2004

Attorney Docket: Solx 4 US  
Art Unit: 1792  
Examiner: G. Ragesh Rao  
Date: April 23, 2009

For: SYSTEM FOR CONTINUOUS  
GROWING OF MONOCRYSTALLINE  
SILICON

## AMENDMENT

Assistant Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Sir:

In response to the Official Action mailed November 25, 2008, please amend the application as follows.

desired level without vertical travel of the crucible; and separately controllable heater elements are provided adjacent the crucible for transferring a desired amount of thermal energy to the adjacent portion of the crucible for providing a controllable thermal distribution across the crucible and at the crystal / melt interface. When, as here, the references fail to suggest the foregoing structure, claim 19 is believed to patentably distinguish over the cited combination. Reconsideration and allowance of claim 19 are respectfully requested.

In view of the above amendments and remarks, it is believed that this application is now in condition for allowance and such a notice is respectfully requested.

Respectfully submitted,

By: Michael Hetherington

Michael Hetherington  
Registration No.: 32,357  
Attorney for Applicant

Tel: 650 533 6936  
Fax: 650 851 9192  
Mailing Address:  
P. O. Box 61047  
Palo Alto, CA 94306